

20V Dual N-Channel MOSFET



SOP-8

Pin Definition:

1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2 4. Gate 2 5. Drain 2 PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
	30 @ V _{GS} = 4.5V	6.0
20	40 @ V _{GS} = 2.5V	5.2
	41 @ V _{GS} = 2.0V	2.0
	42 @ V _{GS} = 1.8V	2.0

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

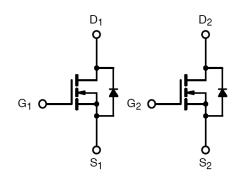
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing		
TSM9428DCS RL	SOP-8	2.5Kpcs / 13" Reel		

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	6	А	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	20	Α	
Continuous Source Current (Diode Condu	Diode Conduction) ^{a,b} I _S		1.7	А	
Maximum Daviar Dissipation	Ta = 25°C	В	2.5	W	
Maximum Power Dissipation	Ta = 70°C	P _D	1.6		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	R⊖ _{JF}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



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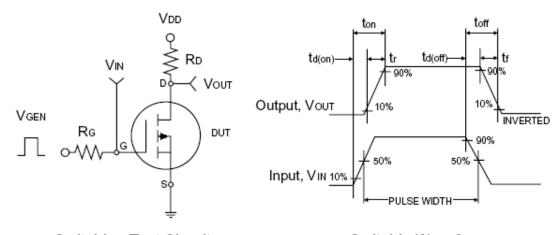


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	V _{GS(TH)}	0.45	0.65	0.85	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}			1.0	uA
On-State Drain Current	V _{DS} ≥5V, V _{GS} = 4.5V	I _{D(ON)}	20			Α
	$V_{GS} = 4.5V, I_D = 6.0A$			23	30	mΩ
Drain Source On State Desigtance	V _{GS} = 2.5V, I _D = 5.2A] _B		28	40	
Drain-Source On-State Resistance	$V_{GS} = 2.0V, I_D = 2.0A$	$R_{DS(ON)}$		29	41	
	V _{GS} = 1.8V, I _D = 2.0A			30	42	
Forward Transconductance	$V_{DS} = 10V, I_D = 6.0A$	g _{fs}		24		S
Diode Forward Voltage	$I_S = 1.0A, V_{GS} = 0V$	V_{SD}			1.2	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = 10V, I_D = 6A,$	Q_g		11	14	
Gate-Source Charge	$V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$	Q_gs		1.5		nC
Gate-Drain Charge	V _{GS} = 4.5V	Q_{gd}		2.1		
Input Capacitance	V - 40V V - 0V	C _{iss}		900		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		140		pF
Reverse Transfer Capacitance	- 1 = 1.0WIDZ	C _{rss}		100		
Switching ^c		•				
Turn-On Delay Time	V 40V D 400	t _{d(on)}		0.53	0.8	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 10\Omega,$	t _r		1.4	2.2	20
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 4.5V,$	t _{d(off)}		13.5	20	nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		5.9	9	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

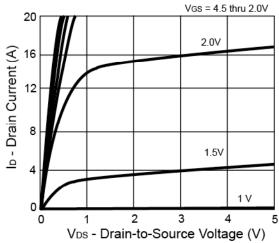


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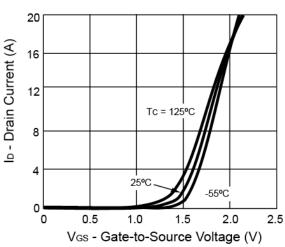


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

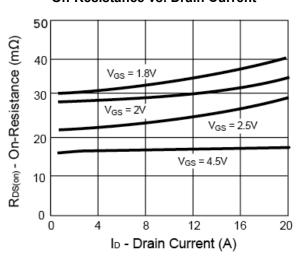
Output Characteristics



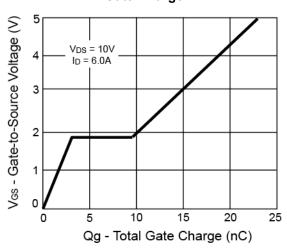
Transfer Characteristics



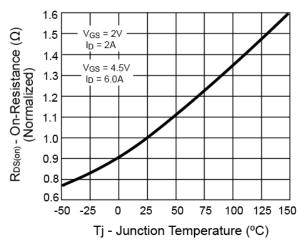
On-Resistance vs. Drain Current



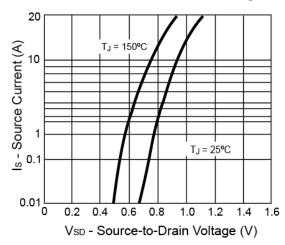
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



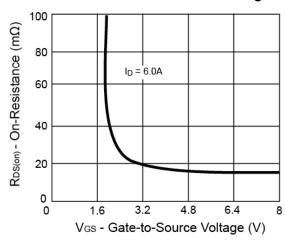


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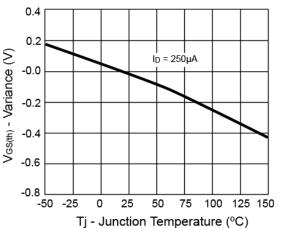


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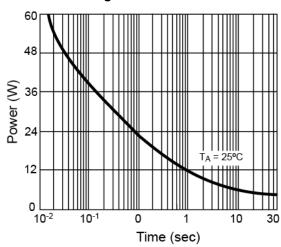
On-Resistance vs. Gate-Source Voltage



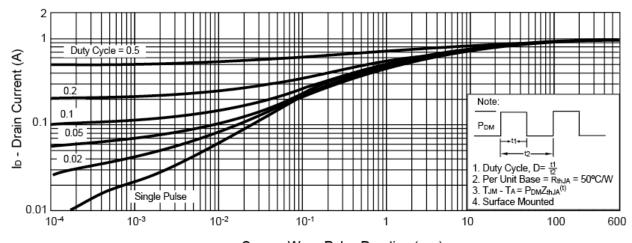
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



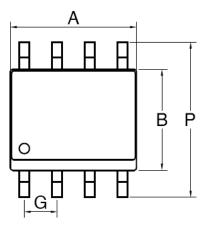
Square Wave Pulse Duration (sec)



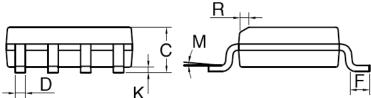
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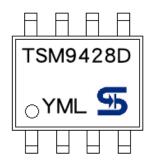
SOP-8 Mechanical Drawing



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05BSC		
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code

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Version: D07



TSM9428D 20V Dual N-Channel MOSFET

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